



100V PNP HIGH VOLTAGE TRANSISTOR IN TO252 (DPAK)

Description

This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

Features

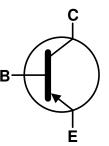
- BV_{CFO} > -100V
- I_C = -3A High Continuous Collector Current
- I_{CM} = -5A Peak Pulse Current
- Ideal for Power Switching or Amplification Applications
- Complementary NPN Type: MJD31CUQ
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

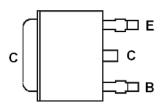
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202. Method 208 @3
- Weight: 0.34 grams (Approximate)







Device Schematic



Pin Out Configuration Top View

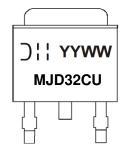
Ordering Information (Notes 4 & 5)

Part number	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MJD32CHQ-13	Automotive	MJD32CU	13	16	2 500

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-120	V
Collector-Emitter Voltage	V_{CEO}	-100	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	А
Peak Pulse Collector Current	I _{CM}	-5	A
Continuous Base Current	lΒ	-1	A
Power Dissipation	P_{D}	15	W

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
	(Note 6)		3.9	
Power Dissipation	(Note 7)	P _D	2.1	W
	(Note 8)		1.6	
	(Note 6)		32	
Thermal Resistance, Junction to Ambient Air	(Note 7)	R_{\thetaJA}	59	0000
	(Note 8)		80	°C/W
Thermal Resistance, Junction to Leads	(Note 9)	$R_{ heta JL}$	3.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

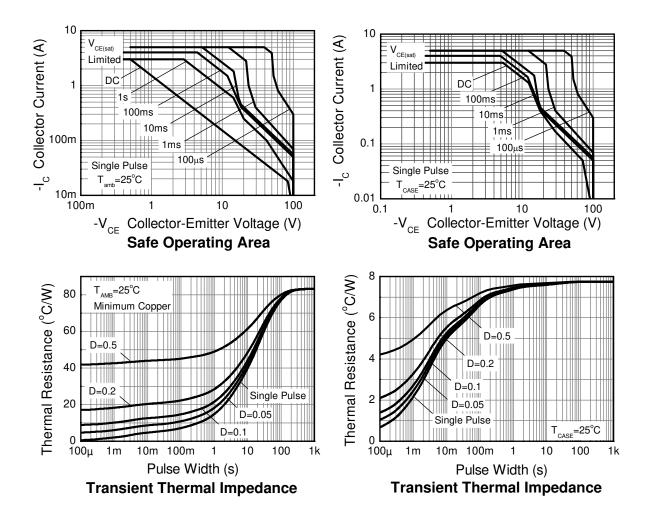
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 6. For a device mounted with the exposed collector pad on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 7. Same as note (6), except mounted on 25mm x 25mm 1oz copper.
- 8. Same as note (6), except mounted on minimum recommended pad (MRP) layout.
- Thermal resistance from junction to solder-point (on the exposed collector pad).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics





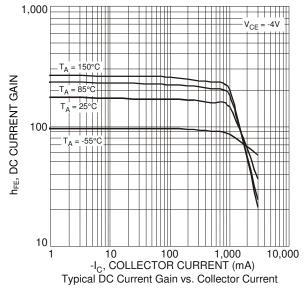
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

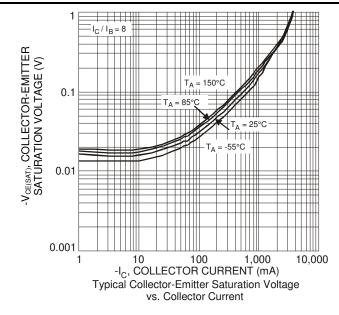
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-120	_	_	V	I _C = -20μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-100	_	_	V	$I_C = -30mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	V	$I_E = -100 \mu A$
Collector-Base Cut-off Current	I _{CBO}	_	_	-1	μΑ	$V_{CB} = -100V$
Collector Cut-off Current	I _{CEO}	=	_	-1	μΑ	$V_{CE} = -60V$
Collector Cut-off Current	I _{CES}	-	_	-1	μΑ	$V_{CE} = -100V$
Emitter Cut-off Current	I _{EBO}	_	_	-1	μΑ	$V_{EB} = -5V$
Oallandan Frailtan Oak matian Waltana		-	_	-300	mV	$I_C = -1A$, $I_B = -100mA$
Collector-Emitter Saturation Voltage (Note 11)	V _{CE(sat)}	_	_	-500	mV	$I_C = -2A$, $I_B = -200mA$
(Note 11)		=	_	-700	mV	$I_C = -3A$, $I_B = -375mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	-1.2	V	$I_C = -2A$, $I_B = -200mA$
Base-Emitter Turn-On Voltage (Note 11)	V	-	_	-950	mV	$I_C = -1A$, $V_{CE} = -2V$
Dase-Emilier rum-On voltage (Note 11)	V _{BE(on)}	=	_	-1.4	V	$I_C = -3A$, $V_{CE} = -4V$
DC Current Gain (Note 11)	h	25		_		$V_{CE} = -4V, I_{C} = -1A$
Do Current Gain (Note 11)	h _{FE}	10	1	50		$V_{CE} = -4V$, $I_C = -3A$
Current Signal Current Gain	H _{fe}	20	_	-	-	$V_{CE} = -10V$, $I_{C} = -0.5A$, $f = 1kHz$
Current Gain-Bandwidth Product	f _T	3.0	_	_	MHz	$I_C = -0.5A$, $V_{CE} = -10V$, $f = 1MHz$

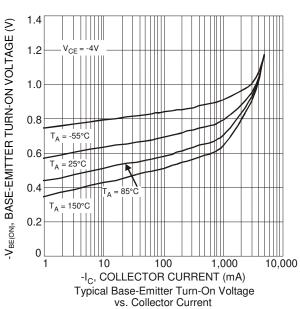
Note: 11. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

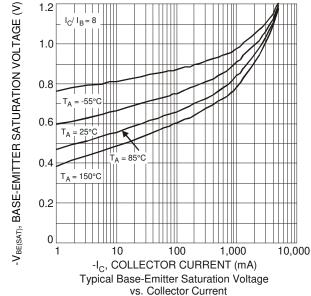


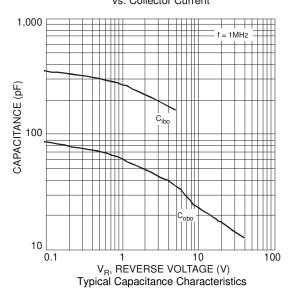
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)









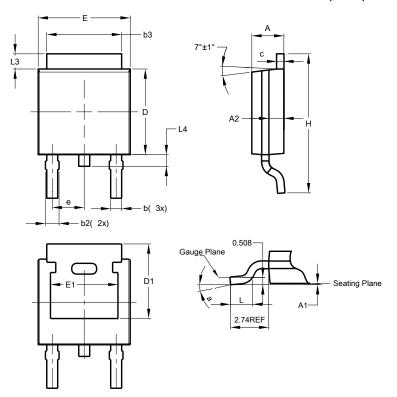




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

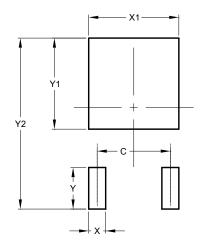


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
A 1	0.00	0.13	0.08		
A2	0.97	1.17	1.07		
q	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.46	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21	-	-		
е	-	-	2.286		
Е	6.45	6.70	6.58		
E1	4.32	-	-		
H	9.40	10.41	9.91		
٦	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°	-		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Χ	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device Terminals and PCB tracking.



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